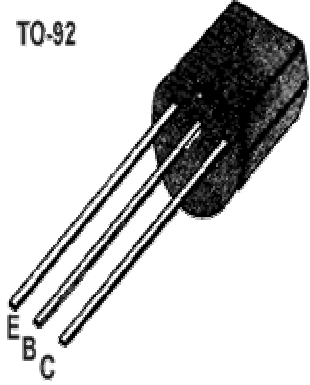


■■ APPLICATION: High Voltage Driver Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V <sub>CB0</sub>	-400	V
Collector-emitter voltage	V <sub>CE0</sub>	-400	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>c</sub>	-300	mA
Collector Power Dissipation	P <sub>c</sub>	625	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h <sub>FE</sub>	50		300		V <sub>CE</sub> = -10V, I <sub>c</sub> = -10mA
Collector Cut-off Current	I <sub>CB0</sub>			-0.1	μA	V <sub>CB</sub> = -400V, I <sub>E</sub> =0
Emitter Cut-off Current	I <sub>EBO</sub>			-0.1	μA	V <sub>EB</sub> = -3V, I <sub>c</sub> =0
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	-400			V	I <sub>c</sub> = -100μA, I <sub>E</sub> =0
Collector-Emitter Breakdown Voltage	BV <sub>CE0</sub>	-400			V	I <sub>c</sub> = -1mA, I <sub>B</sub> =0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5			V	I <sub>E</sub> = -100μA, I <sub>c</sub> =0
Collector-Emitter Saturation Voltage	V <sub>CE(sat)1</sub>			-0.5	V	I <sub>c</sub> = -10mA, I <sub>B</sub> = -1mA
	V <sub>CE(sat)2</sub>			-0.75	V	I <sub>c</sub> = -50mA, I <sub>B</sub> = -5mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>			-0.75	V	I <sub>c</sub> = -10mA, I <sub>B</sub> = -1mA
Common Base Output Capacitance	C <sub>ob</sub>			6	PF	V <sub>CB</sub> = -20V, I <sub>E</sub> =0, f = 1MHz
Gain bandwidth product	f <sub>t</sub>	50			MHz	I <sub>c</sub> = -10mA, V <sub>CE</sub> = -20V, f = 100MHz

■■ h<sub>FE</sub> Classification

Classification

h<sub>FE</sub> 50~300